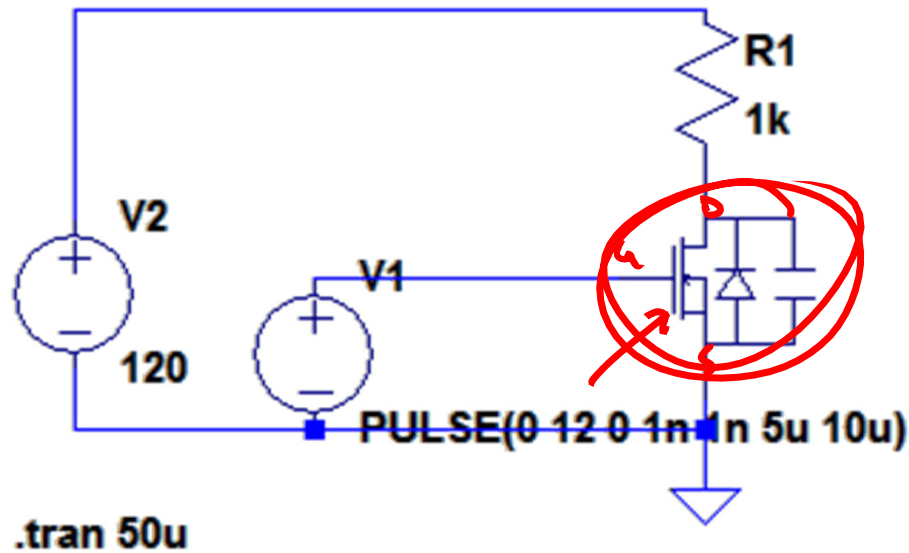


Simulation Modeling

Circuit Simulation

- LTSpice
 - Other tools accepted, but not supported
- Choose model type (switching, averaged, dynamic)
- Supplement analytical work rather than repeating it
- Show results which clearly demonstrate what matches and what does not with respect to experiments (i.e. ringing, slopes, etc.)

LTSpice Modeling Examples

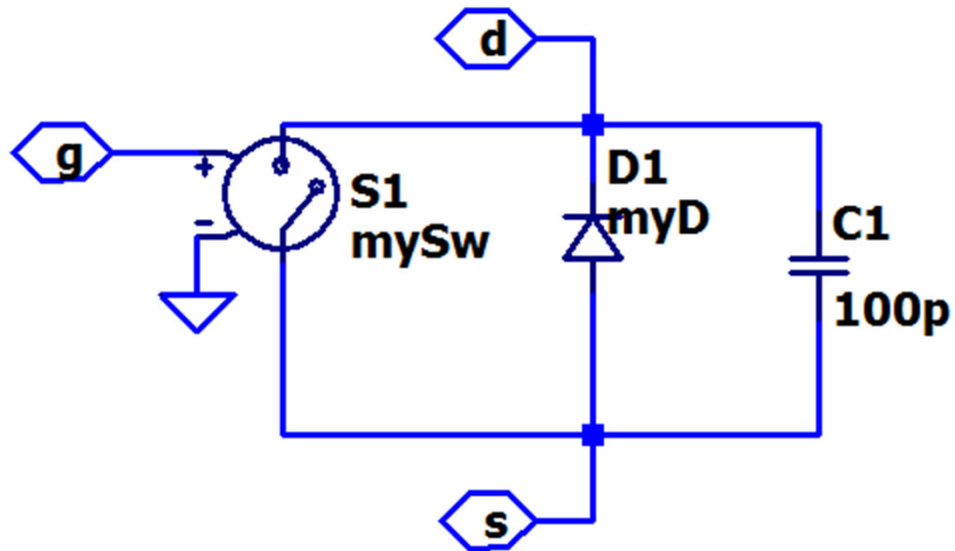


- Example files added to course materials page
 - Custom model
 - VDMOS model
 - Manufacturer Model

Custom Transistor Model

```
.model myD D(n=.001)
```

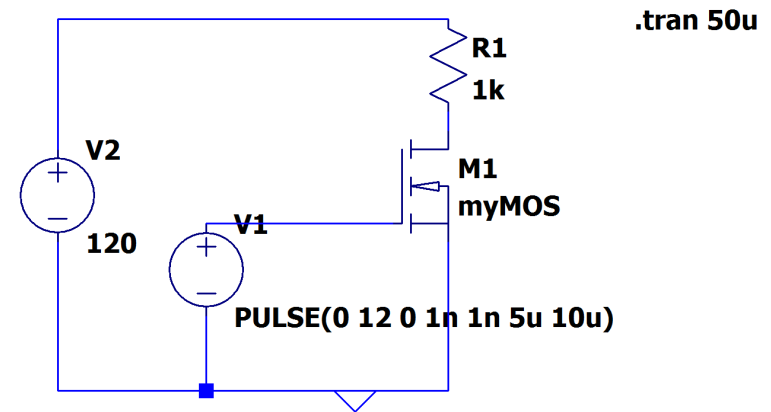
```
.model mySw SW(Ron=10m Roff=1G Von=1 Voff = .5 )
```



VDMOS Model

Name	Description	Units	Default	Example
Vto	Threshold voltage	V	0	1.0
Kp	Transconductance parameter	A/V ²	1.	.5
Phi	Surface inversion potential	V	0.6	0.65
Lambda	Channel-length modulation	1/V	0.	0.02
mtriode	Conductance multiplier in triode region(allows independent fit of triode and saturation regions)	-	1.	2.
subthres	Current(per volt Vds) to switch from square law to exponential subthreshold conduction	A/V	0.	1n
BV	Vds breakdown voltage	V	Infin.	40
IBV	Current at Vds=BV	A	100pA	1u
NBV	Vds breakdown emission coefficient	-	1.	10
Rd	Drain ohmic resistance	Ω	0.	1.
Rs	Source ohmic resistance	Ω	0.	1.
Rg	Gate ohmic resistance	Ω	0.	2.
Rds	Drain-source shunt resistance	Ω	Infin.	10Meg
Rb	Body diode ohmic resistance	Ω	0.	.5
Cio	Zero-bias body diode	F	0.	1n

.model myMOS VDMOS(nchan Rg=3 Rd=14m Rs=10m Vto=-.8 Kp=32 + Cgdmax=.5n Cgdmin=.07n Cgs=.9n Cjo=.26n Is=26p Rb=17m)



- Note: any other parameters **ignored**
 - E.g. ron = 3m Qg = 1n mfg = Infineon

Manufacturer Device Model

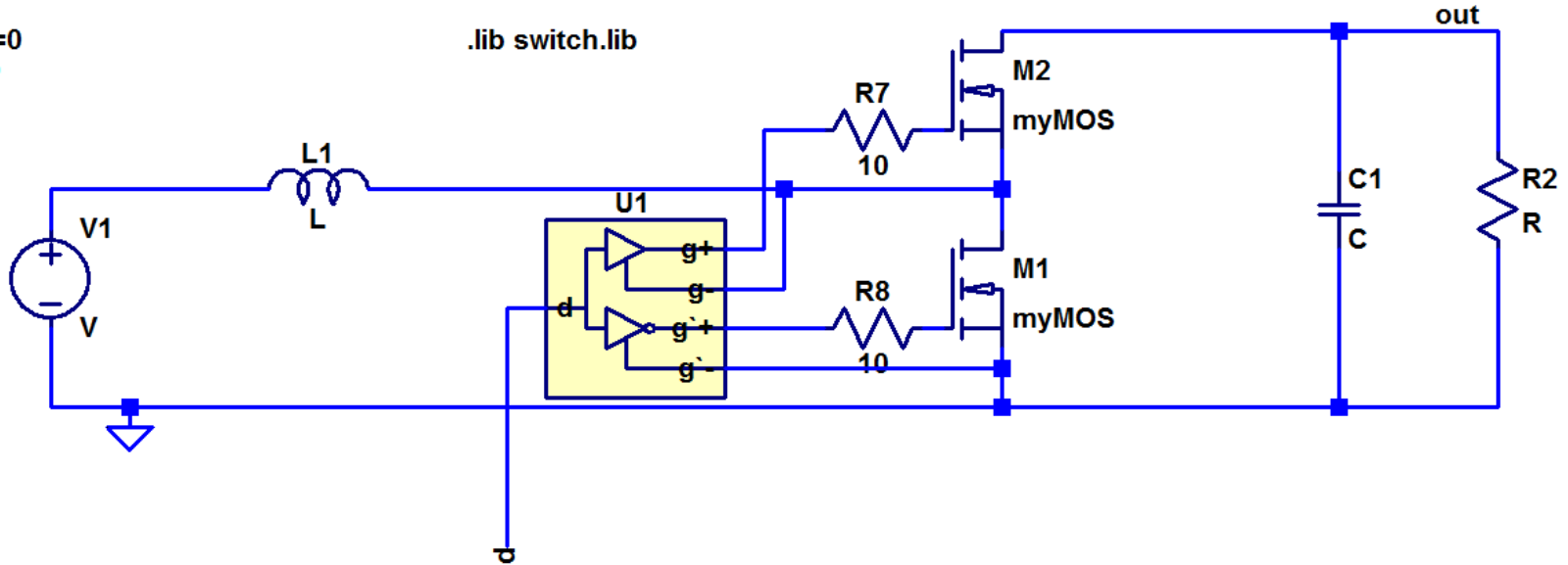
- Text-only netlist model of device including additional parasitics and temperature effects
- May slow or stop simulation if timestep and accuracy are not adjusted appropriately

Full Switching Simulation

```
.tran 1 .model myMOS VDMOS(Rg=1 Vto=4.5 Rd=14m Rs=10m Rb=17m Kp=30 Cgdmax=.5p Cgdmin=.05n Cgs=.2n Cjo=.03n Is=88p)
```

```
.ic V(out)=0  
.ic I(L1)=0
```

```
.lib switch.lib
```

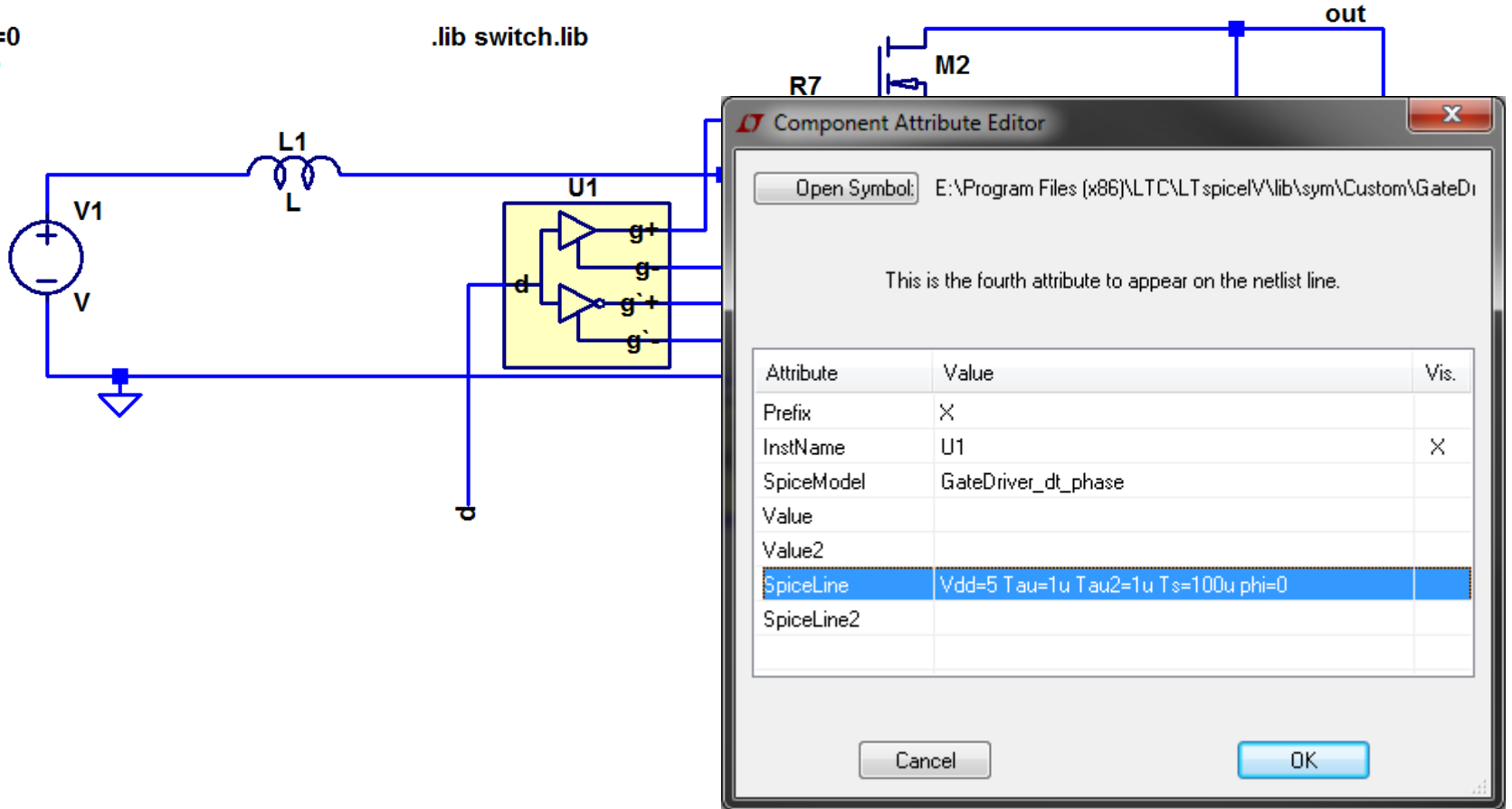


Full Switching Simulation

```
.tran 1 .model myMOS VDMOS(Rg=1 Vto=4.5 Rd=14m Rs=10m Rb=17m Kp=30 Cgdmax=.5p Cgdmin=.05n Cgs=.2n Cjo=.03n Is=88p)
```

```
.ic V(out)=0  
.ic I(L1)=0
```

```
.lib switch.lib
```



Experiment 2

Experiment 3

Experiment Procedure

[Prelab Assignment](#)

[Experiment 3 Procedure](#)

Experiment 3 Components

[Contents of the Experiment 3 Parts Kit](#)

[Contents of the Magnetics Library](#)

[Breakout Board Schematics and Layout \(pdf\)](#)

[Breakout Board Schematics and PCB Layout \(Altium\)](#)

Reference Materials

[Designing Bootstrap Networks](#)

[Power Converter Layout](#)

[Reduction of Ringing in Power Converters \(TI App. Note\)](#)

[RMS Values of Commonly Observed Waveforms](#)

LTSpice Example Files

[Examples of power semiconductor modeling using custom or manufacturer models](#)

[Example Switching and Averaged Boost LTSpice Models](#)

Magnetics Design

[Filter Inductor Design Notes](#)

[Kg Method Step-by-Step](#)

[Kgfe Method Step-by-Step](#)

[Overview of Empirical Core Loss Calculation Techniques](#)

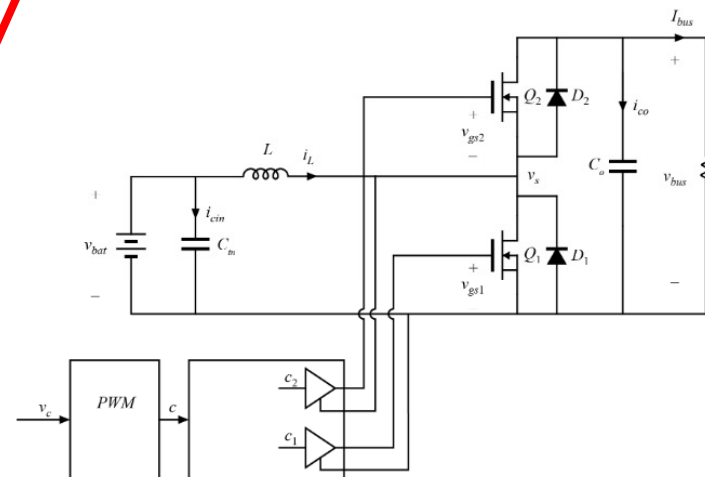
[Overview of Empirical State of Core Loss Prediction](#)

[Magnetics Design Tables](#)

[AWG Chart](#)

Experiment 4

Available on Exp 3 Webpage



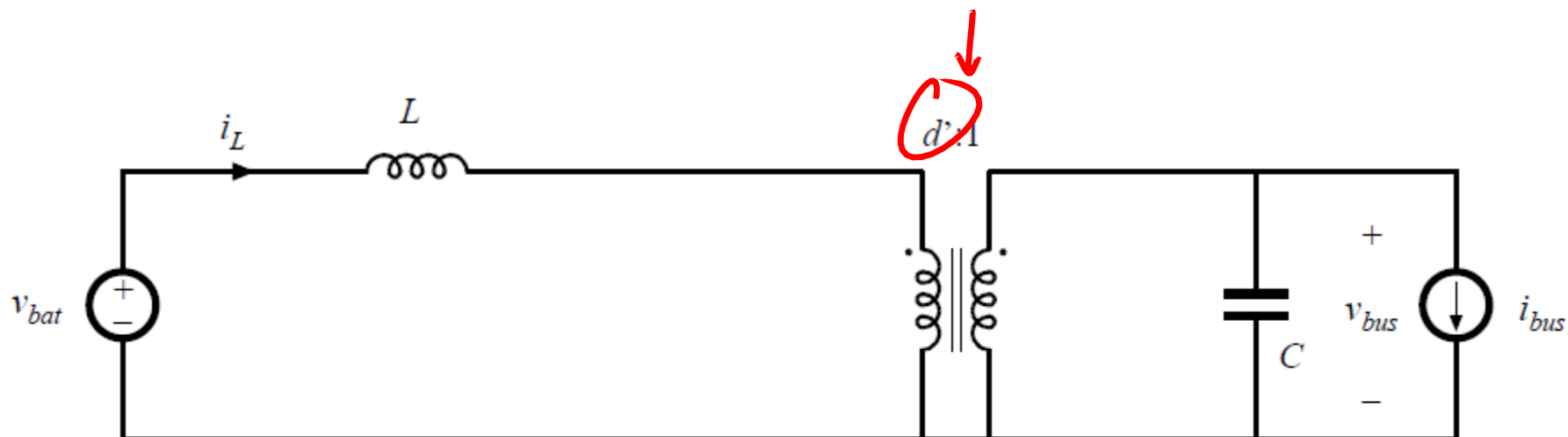
Full Switching Model

- Gives valuable insight into circuit operation
 - Understand expected waveforms
 - Identify discrepancies between predicted and experimental operation
- Slow to simulate; significant high frequency content
- Cannot perform AC analysis

Averaged Switch Modeling: Motivation

- A *large-signal, nonlinear* model of converter is difficult for hand analysis, but well suited to simulation across a wide range of operating points
- Want an *averaged* model to speed up simulation speed
- Also allows linearization (AC analysis) for control design

Nonlinear, Averaged Circuit



$$L \frac{d\langle i_L \rangle}{dt} = \langle v_{bat} \rangle - \underbrace{d(t) \cdot v_{bus}(t)}_{(1-d)\langle v_{bus} \rangle}$$

$$C \frac{d\langle v_{bus} \rangle}{dt} = (1-d)\langle i_L \rangle - \langle i_{bus} \rangle$$

DC analysis

$$\frac{dx}{dt} = \phi$$

↓
DC steady-state
averaged
behavior

AC analysis

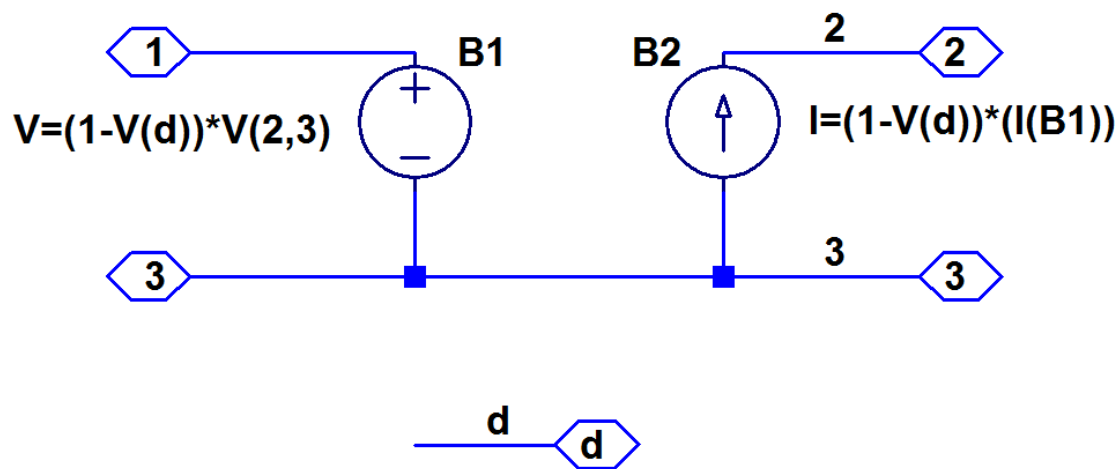
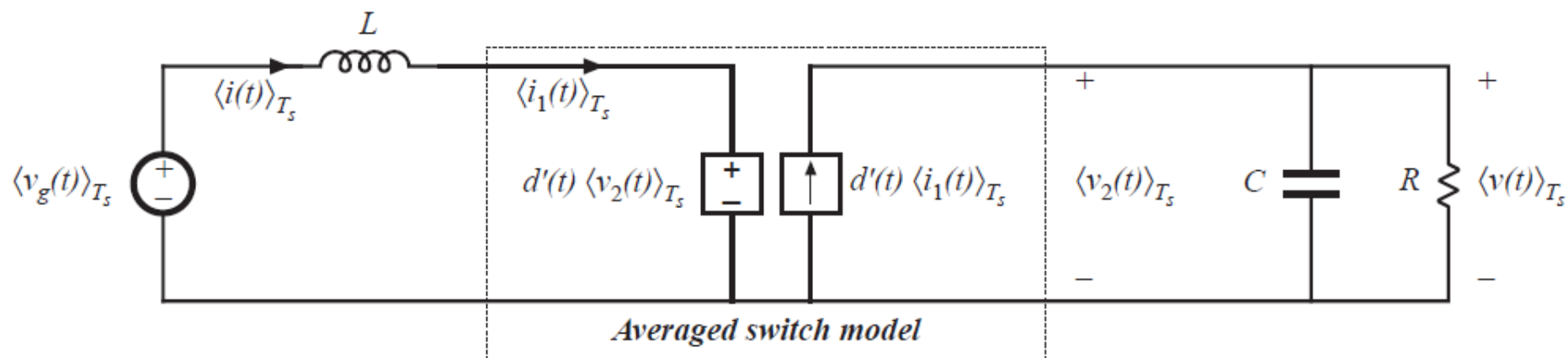
small-signal
analysis

$$x(t) = X + \hat{x}$$

↓
Averaged, linear
small-signal
equations

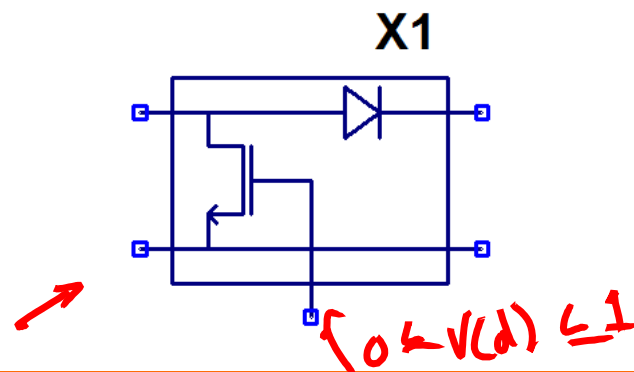
for simulation: no need to linearize.

Implementation in LTSpice

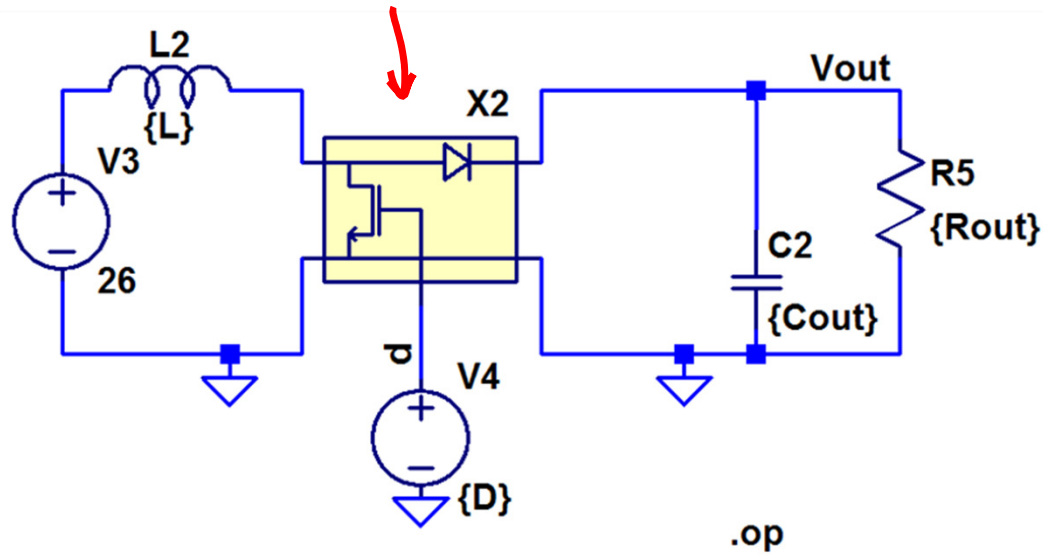


$$\langle v_1(t) \rangle_{T_s} = d'(t) \langle v_2(t) \rangle_{T_s}$$

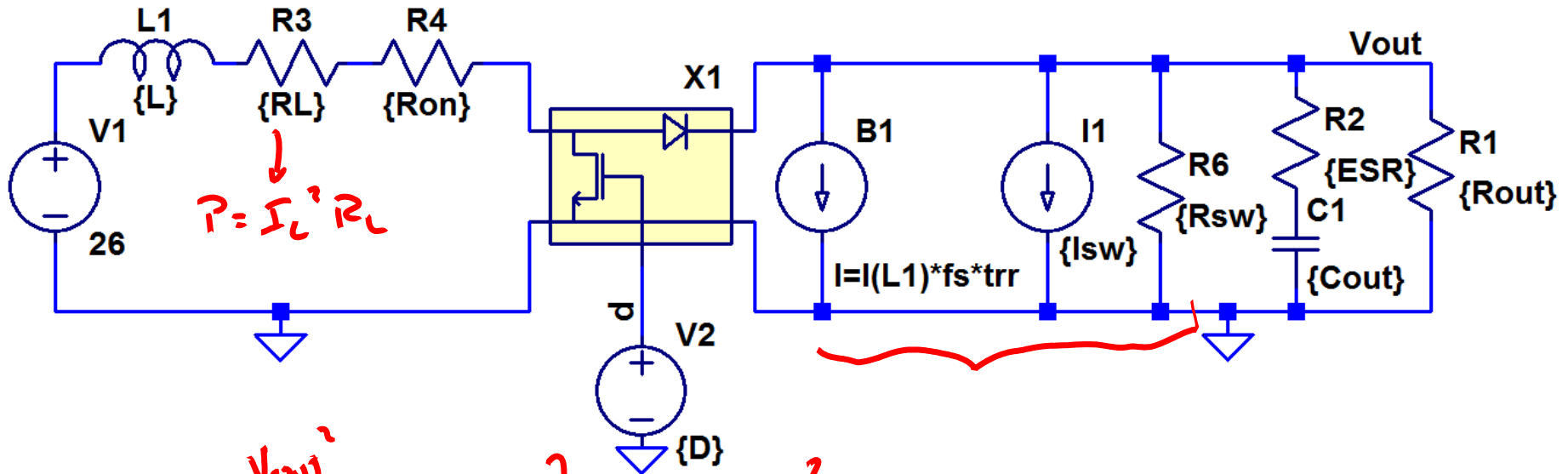
$$\langle i_2(t) \rangle_{T_s} = d'(t) \langle i_1(t) \rangle_{T_s}$$



Averaged Switch Model



Averaged Model With Losses



$$P_{R_{sw}} = \frac{V_{out}^2}{R_{sw}}$$

$$P_{loss} = \frac{1}{2} C_{oss} V_{out}^2 f_s$$

$$R_{sw} = \frac{2}{C_{oss} f_s}$$

```
.op
.param Rout = 10
.step param Rout 10 100 10
```

What known error(s) will be present in loss predictions with this model?